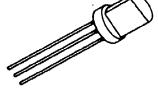
20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.



Silicon Transistor

2N3721 is a NPN silicon transistor intended for general purpose applications. The planar passivated construction assures excellent device stability and life. This high performance, high value device is made possible by utilizing advanced manufacturing techniques and epoxy encapsulation.



TELEPHONE: (973) 376-2922

(212) 227-6005

FAX: (973) 376-8960

absolute maximum ratings: (25°C) (unless otherwise specified) Voltages

| Collector to emitter | V _{CEO} | 18 | V | | - <u>- 205</u> .195 - |
|-------------------------------------|------------------|-------------------|-------------------------------|---|---|
| Emitter to base | V _{EBO} | 5 | V | | - <u>190</u> - |
| Collector to base | V _{CBO} | 18 | V NOTE 1: Lead | d diameter is controlled in the n.070 and .250 from the seat- | |
| Current | | | ing plane. Be max. of .021 | etween .250 and end of lead a | <u>.075</u> .055 <u>.265</u> .225 |
| Collector (steady state) | I _C , | 100 | mA max. or .021 | is neig. | .225 |
| Dissipation | | | | | JUU .500 SEATING |
| Total Power (Free air @ 25°C) | P _{T**} | 360 | mW ALL DIMEN | IN INCHES AND ARE | |
| Total Power (Free air @ 55°C) | P _T | 260 | mW | | 050±.005 |
| Temperature | | | | 3 LEADS | |
| Storage | T _{STG} | -55 to | +125°C | .017 +.002 001 | |
| Operating | T, | | +125° C | (NOTE I) | |
| * Determined from nower limitations | due to seturati | ion voltage at th | is ourrant | | |

* Determined from power limitations due to saturation voltage at this current.

** Derate 2.67 mW/°C increase in ambient temperature above 25°C.

electrical characteristics: (25°C) (unless otherwise specified)

| DC Characteristics Collector cutoff current: (VCB = 18V) (VCB = 18V, TA=100°C) Emitter cutoff current: (VEB=5V) Small Signal Characteristics | I _{cbo} I _{cbo} I _{ebo} | Min. | Тур. | Мах. 0.5 15 0.5 | Units μΑ μΑ μΑ |
|--|--|------|------|--------------------------|-------------------------|
| Forward current transfer ratio: (VCE=) | 10V, | | | | |
| $IC = 2 ma, f = lk Hz^{\dagger}$ | h _{FE} | 60 | | 660 | |
| Input impedance: | | | | | |
| (VCE=10V, IC=2mA, f=lk Hz) | h _{IB} | | 15 | | ohms |
| High Frequency Characteristics | | | | | |
| Collector capacitance: (VCB=10V, IE= | 0, | | | | |
| f=l MHz) | C _{cb} | 4.5 | 7 | 10 | pF |
| Gain bandwidth product: | | | | | F - |
| (IC=4mA, VCB=5V) | f _t | | 120 | | MHz |

† Hz=Hertz, equivalent to cycles per second.



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